

CENTRAL INTELLIGENCE AGENCY
INFORMATION REPORT

REPORT [Redacted]
CD NO. [Redacted]

COUNTRY East Germany

DATE DISTR. 11 February 1955

SUBJECT Transistor [Redacted] Werk fuer
Bauelemente [Redacted] hnik "Carl
von Ossietz [Redacted]

NO. OF PAGES 2 25X1

PLACE ACQUIRED [Redacted]
DATE OF INFO. [Redacted]

NO. OF ENCLS. (LISTED BELOW)

SUPPLEMENT TO REPORT NO. 25X1

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THIS IS UNEVALUATED INFORMATION 25X1

[Redacted] technik "Carl von Ossietzky" (formerly the Dralwid plant) in July 1954.
[Redacted] of transistors [Redacted] was [Redacted] done at the [Redacted] *Hans* 25X1
[Redacted] communication Engineering Plant under the supervision of [Redacted]
[Redacted] inued at this enterprise [Redacted] rred to Dr. [Redacted]
[Redacted] laboratory at the Dralwid [Redacted] Falter developed
transis [Redacted] germanium basis with an [Redacted] indium. This
development work was scheduled to be completed by the end of October
1954. Technical specifications for this type of transistor included:

Voltage : 50 to 100 V
Power output : up to 20 mW
Input
[Redacted] (regel): 200 mV
Limit frequency: 1 to 3 [Redacted]
Amplification : 50 to [Redacted]
Sensitivity : 50 to 60 db (total resistance in relation to
noise resistance measured at the equivalent input
resistance)

b. Development of two types of transistors for oscillators and amplifiers.
It was also intended further to develop these transistors for
frequencies from 5 to 10 Mc.

c. Development of germanium diodes in which [Redacted]
pass voltage (Durchlass-Spannung) were [Redacted]
at a current intensity of 10 mA. It is [Redacted]
diodes, one for 2 and one for 5 mA. The [Redacted]

d. Experiments to manufacture resistances which have a boron-treated
carbon layer. These resistances are believed to be much more efficient
and much easier to manufacture. Moreover, they are much more sensitive
to humidity than [Redacted] resistances. Their [Redacted]
a [Redacted]

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